

## COMPLEMENTARY SILICON POWER TRANSISTORS

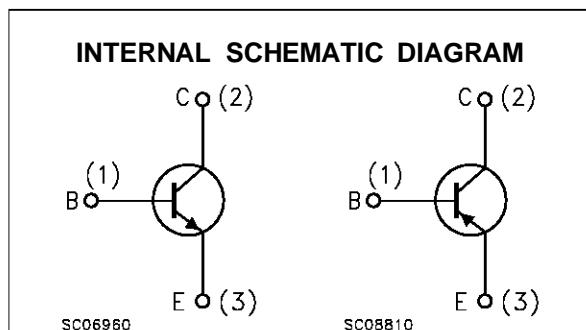
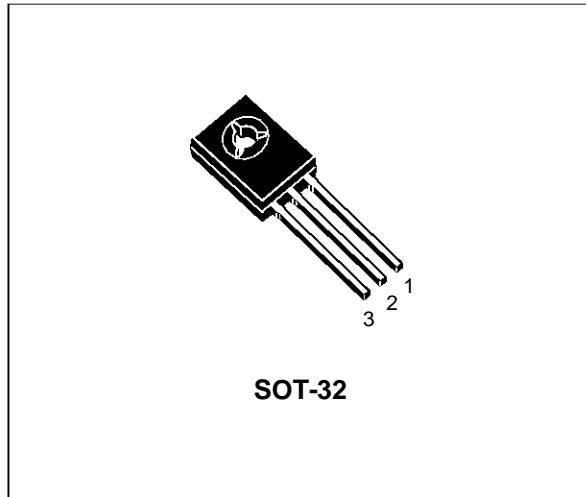
- SGS-THOMSON PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES

### DESCRIPTION

The BD433, BD435, and BD437 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package, intended for use in medium power linear and switching applications.

The BD433 is especially suitable for use in car-radio output stages.

The complementary PNP types are BD434, BD436, and BD438 respectively.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		NPN	BD433	BD435	BD437	
PNP	BD434	BD436	BD438			
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	22	32	45	45	V
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	22	32	45	45	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	22	32	45	45	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )		5		5	V
$I_C$	Collector Current		4		4	A
$I_{CM}$	Collector Peak Current ( $t \leq 10 \text{ ms}$ )		7		7	A
$I_B$	Base Current		1		1	A
$P_{tot}$	Total Dissipation at $T_c \leq 25^\circ\text{C}$		36		36	W
$T_{stg}$	Storage Temperature		-65 to 150		-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature		150		150	$^\circ\text{C}$

For PNP types voltage and current values are negative.

## BD433/434/435/436/437/438

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	3.5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	100	°C/W

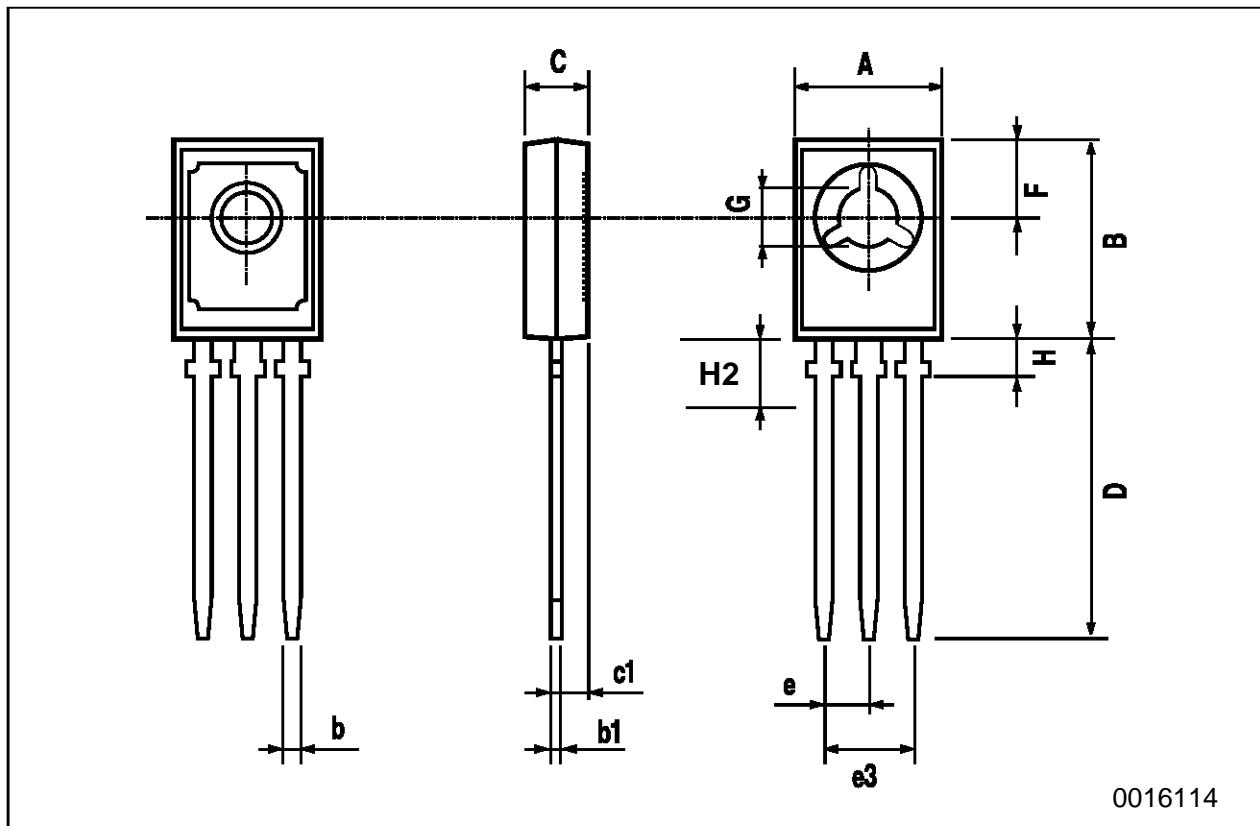
### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>cBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	for BD433/434	V <sub>CB</sub> = 22 V			100	µA
		for BD435/436	V <sub>CB</sub> = 32 V			100	µA
		for BD437/438	V <sub>CB</sub> = 45 V			100	µA
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	for BD433/434	V <sub>CE</sub> = 22 V			100	µA
		for BD435/436	V <sub>CE</sub> = 32 V			100	µA
		for BD437/438	V <sub>CE</sub> = 45 V			100	µA
I <sub>EB0</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V				1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	for BD433/434	22			V
			for BD435/436	32			V
			for BD437/438	45			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2 A	I <sub>B</sub> = 0.2 A			0.5	V
			for BD433/434			0.2	V
			for BD435/436			0.5	V
			for BD437/438			0.6	V
V <sub>BE*</sub>	Base-Emitter Voltage	I <sub>C</sub> = 10 mA I <sub>C</sub> = 2 A	V <sub>CE</sub> = 5 V V <sub>CE</sub> = 1 V for BD433/434 for BD435/436 for BD437/438		0.58		V
						1.1	V
						1.1	V
						1.2	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 10 mA  I <sub>C</sub> = 500 mA I <sub>C</sub> = 2 A	V <sub>CE</sub> = 5 V for BD433/434 for BD435/436 for BD437/438  V <sub>CE</sub> = 1 V V <sub>CE</sub> = 1 V for BD433/434 for BD435/436 for BD437/438	40 40 30 85	130 130 130 140		
h <sub>FE1</sub> /h <sub>FE2*</sub>	Matched Pair	I <sub>C</sub> = 500 mA	V <sub>CE</sub> = 1 V			1.4	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> = 250 mA	V <sub>CE</sub> = 1 V	3			MHz

\* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

## SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	7.4		7.8	0.291		0.307
B	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
C	2.4		2.7	0.040		0.106
c1	1.0		1.3	0.039		0.050
D	15.4		16.0	0.606		0.629
e		2.2			0.087	
e3	4.15		4.65	0.163		0.183
F		3.8			0.150	
G	3		3.2	0.118		0.126
H			2.54			0.100
H2		2.15			0.084	



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